

Product Overview

FDMS3660S: Asymmetric Dual N-Channel PowerTrench® Power Stage MOSFET 30V

For complete documentation, see the data sheet.

This device includes two specialized N-Channel MOSFETs in a dual PQFN package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET (Q2) have been designed to provide optimal power efficiency.

Features

- Q1: N-Channel Max $r_{DS(on)}$ = 8 m Ω at $V_{GS} = 10$ V, $I_D = 13$ A Max $r_{DS(on)}$ = 11 m Ω at $V_{GS} = 4.5$ V, $I_D = 11$ A
- Q2: N-Channel Max $r_{DS(on)}$ = 1.8 m Ω at $V_{GS} = 10$ V, $I_D = 30$ A Max $r_{DS(on)}$ = 2.2 m Ω at $V_{GS} = 4.5$ V, $I_D = 27$ A
- Low inductance packaging shortens rise/fall times, resulting in lower switching losses
- MOSFET integration enables optimum layout for lower circuit inductance and reduced switch node ringing
- RoHS Compliant

Applications

- Notebook PC

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DSS}^{(BR)}$ Min (V)	V_{GS}^{Max} (V)	$V_{GS}^{(th)}$ Max (V)	I_D^{Max} (A)	P_D^{Max} (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m Ω)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m Ω)	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (m Ω)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	C_{iss} Typ (pF)	Package Type
FDMS3660S	0.614	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Dual	30	12	Q1: 2.7, Q2: 2.2	Q1: 13.0, Q2: 30.0	Q1:2.2, Q2: 2.5	-	Q1: 11.0, Q2: 2.2	Q1: 8, Q2: 1.8	17	29	4130	PQFN-8

For more information please contact your local sales support at www.onsemi.com.

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